

isc Silicon NPN Power Transistor

BU2527AX

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 800V$ (Min)
- High Switching Speed

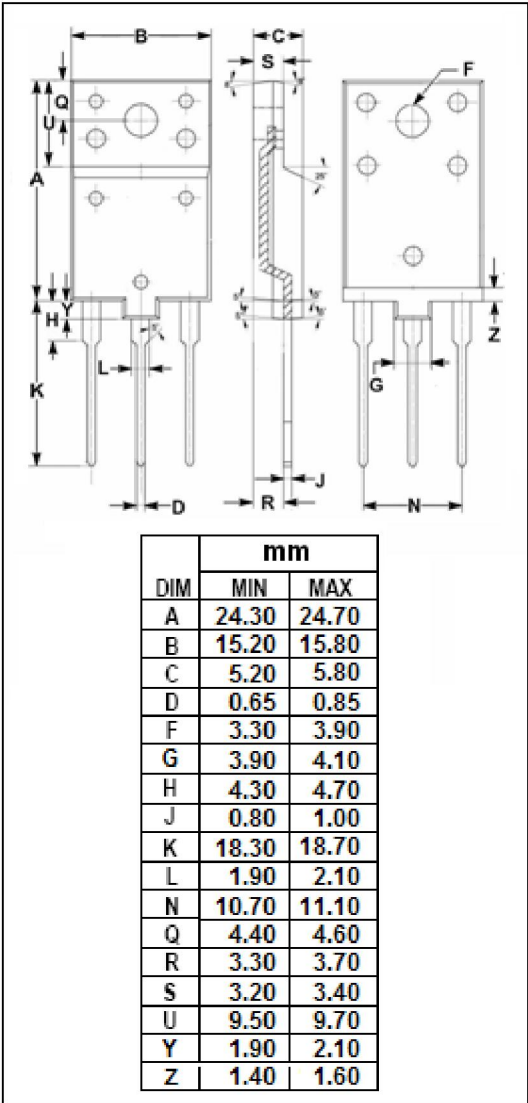
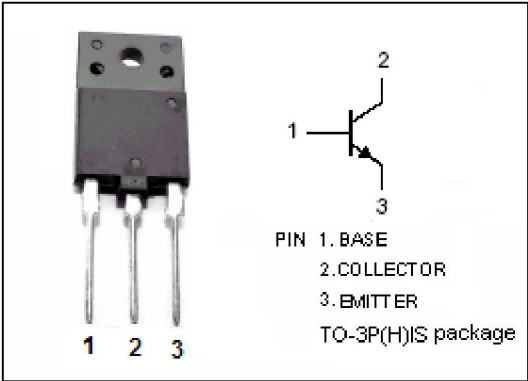
APPLICATIONS

- Designed for use in horizontal deflection circuits of high resolution monitors.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector- Emitter Voltage($V_{BE} = 0$)	1500	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	7.5	V
I_C	Collector Current- Continuous	12	A
I_{CM}	Collector Current-Peak	30	A
I_B	Base Current- Continuous	8	A
I_{BM}	Base Current-Peak	12	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	45	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	2.8	$^{\circ}C/W$



isc Silicon NPN Power Transistor**BU2527AX****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 100mA; I _B = 0, L= 25mH	800			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 1mA; I _C = 0	7.5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 6A; I _B = 1.2A			5.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 6A; I _B = 1.2A			1.3	V
I _{CES}	Collector Cutoff Current	V _{CE} = 1500V; V _{BE} = 0 V _{CE} = 1500V; V _{BE} = 0; T _C =125°C			0.25 2.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 7.5V; I _C = 0			0.25	mA
h _{FE-1}	DC Current Gain	I _C = 1A; V _{CE} = 5V	6		21	
h _{FE-2}	DC Current Gain	I _C = 6A; V _{CE} = 5V	5		9	
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = 10V; f _{test} = 1MHz		145		pF

Switching times

t _{stg}	Storage Time	I _C = 6A, I _{B(end)} = 0.55A; L _B = 0.6 μ H -V _{BB} = 2V; (-dI _B /dt= 3.33A/μ s)			2.0	μ s
t _f	Fall Time				0.2	μ s